

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

# 2SK3561

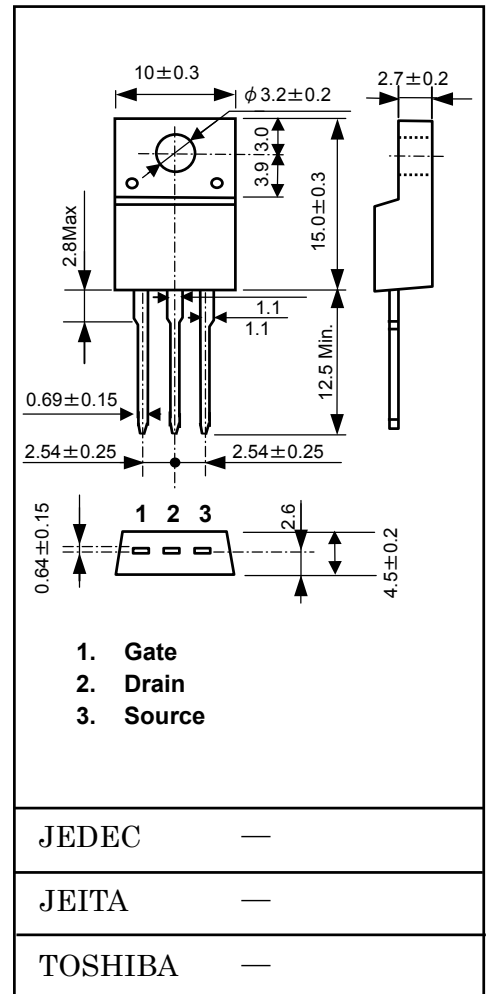
unit : mm

## Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 0.75 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 6.5S$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \mu A$  ( $V_{DS} = 500 V$ )
- Enhancement-mode:  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	500	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	8	A
	Pulse ( $t = 1 ms$ ) (Note 1)	$I_{DP}$	32	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	40	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	312	mJ
Avalanche current		$I_{AR}$	8	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	4	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55~150	$^\circ C$



## Thermal Characteristics

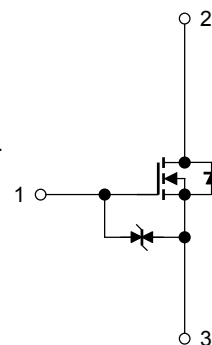
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.125	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

Note 1: Please use devices on conditions that the channel temperature is below  $150^\circ C$ .

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial),  $L = 8.3 mH, I_{AR} = 8 A, R_G = 25 \Omega$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



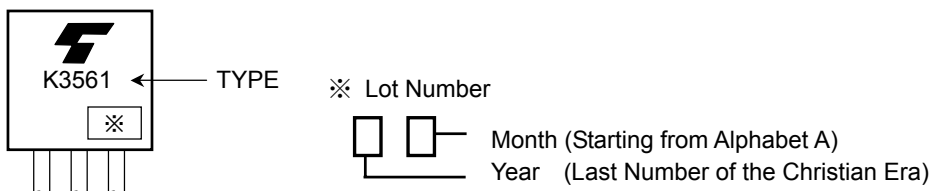
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_D = \pm 10 \mu\text{A}, V_{GS} = 0 \text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$	—	0.75	0.85	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 4 \text{ A}$	3.0	6.5	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1050	—	pF
Reverse transfer capacitance		$C_{rss}$		—	10	—	
Output capacitance		$C_{oss}$		—	110	—	
Switching time	Rise time	$t_r$		—	26	—	ns
	Turn-on time	$t_{on}$		—	45	—	
	Fall time	$t_f$		—	38	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10 \mu\text{s}$	—	130	
Total gate charge		$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$	—	28	—	nC
Gate-source charge		$Q_{gs}$		—	16	—	
Gate-drain charge		$Q_{gd}$		—	12	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	—	8	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	—	32	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 8 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V	
Reverse recovery time	$t_{rr}$	$I_{DR} = 8 \text{ A}, V_{GS} = 0 \text{ V},$	—	1200	—	ns	
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	10	—	$\mu\text{C}$	

## Marking



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